June 1998

National Semiconductor

DS26C32AT/DS26C32AM Quad Differential Line Receiver

General Description

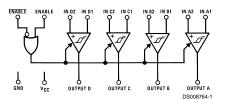
The DS26C32A is a quad differential line receiver designed to meet the RS-422, RS-423, and Federal Standards 1020 and 1030 for balanced and unbalanced digital data transmission, while retaining the low power characteristics of CMOS. The DS26C32A has an input sensitivity of 200 mV over the common mode input voltage range of ±7V. The DS26C32A features internal pull-up and pull-down resistors which prevent output oscillation on unused channels.

The DS26C32A provides an enable and disable function common to all four receivers, and features TRI-STATE [®] outputs with 6 mA source and sink capability. This product is pin compatible with the DS26LS32A and the AM26LS32.

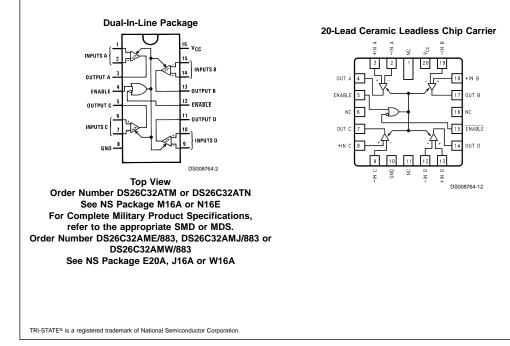
Features

- CMOS design for low power
- ±0.2V sensitivity over input common mode voltage range
- Typical propagation delays: 19 ns
- Typical input hysteresis: 60 mV
- Inputs won't load line when $V_{CC} = 0V$
- Meets the requirements of EIA standard RS-422
- TRI-STATE outputs for connection to system buses
- Available in Surface Mount
- Mil-Std-883C compliant

Logic Diagram



Connection Diagrams



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Absolute Maximum Ratings (Notes 2, 1)

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Supply Voltage (V _{CC})	7V
Common Mode Range (V _{CM})	±14V
Differential Input Voltage (V DIFF)	±14V
Enable Input Voltage (V IN)	7V
Storage Temperature Range (T STG)	–65°C to +150°C
Lead Temperature (Soldering 4 sec.)	260°C
Maximum Power Dissipation at 25°C	(Note 5)
Ceramic "J" Pkg.	2308 mW
Plastic "N" Pkg.	1645 mW
SOIC "M" Pkg.	1190 mW

This device does not meet 2000V ESD rating. (Note 4)					
Maximum Current Per Output	±25 mA				
Ceramic "W" Pkg.	1215 mW				
Ceramic "E" Pkg.	2108 mW				

Operating Conditions

	Min	Max	Units
Supply Voltage (V _{CC})	4.50	5.50	V
Operating Temperature Range (T _A)			
DS26C32AT	-40	+85	°C
DS26C32AM	-55	+125	°C
Enable Input Rise or Fall Times		500	ns

DC Electrical Characteristics

 V_{CC} = 5V ±10% (unless otherwise specified) (Note 1)

Symbol	Parameter	Condition	Conditions			Max	Units
V _{TH}	Minimum Differential	V _{OUT} = V _{OH} or V _{OL}		-200	35	+200	mV
	Input Voltage	$-7V < V_{CM} < +7V$					
R _{IN}	Input Resistance	$V_{IN} = -7V, +7V$	DS26C32AT	5.0	6.8	10	kΩ
		(Other Input = GND)	DS26C32AM	4.5	6.8	11	kΩ
I _{IN}	Input Current	V _{IN} = +10V,	DS26C32AT		+1.1	+1.5	mA
		Other Input = GND	DS26C32AM		+1.1	+1.8	mA
		$V_{IN} = -10V,$	DS26C32AT		-2.0	-2.5	mA
		Other Input = GND	DS26C32AM		-2.0	-2.7	mA
V _{OH}	Minimum High Level	V _{CC} = Min, V _{DIFF} = +1V	$V_{CC} = Min, V_{DIFF} = +1V$				V
	Output Voltage	I _{OUT} = -6.0 mA					
V _{OL}	Maximum Low Level	$V_{CC} = Max, V_{DIFF} = -1$		0.2	0.3	V	
	Output Voltage	I _{OUT} = 6.0 mA					
V _{IH}	Minimum Enable High			2.0			V
	Input Level Voltage						
VIL	Maximum Enable Low					0.8	V
	Input Level Voltage						
l _{oz}	Maximum TRI-STATE®	$V_{OUT} = V_{CC} \text{ or GND},$					
	Output Leakage Current	ENABLE = V_{IL} ,			±0.5	±5.0	μA
		$\overline{ENABLE} = V_{IH}$	ENABLE = V _{IH}				
l _i	Maximum Enable Input	$V_{IN} = V_{CC}$ or GND				±1.0	μA
	Current						
I _{cc}	Quiescent Power	V _{CC} = Max,	DS26C32AT		16	23	mA
	Supply Current	$V_{DIF} = +1V$	DS26C32AM		16	25	mA
V _{HYST}	Input Hysteresis	V _{CM} = 0V			60		mV

AC Electrical Characteristics

$V_{CC} = 5V \pm 10\%$ (Note 3)

Symbol	Parameter	Conditions	Min	Тур	Max		Units
					DS26C32AT	DS26C32AM]
t _{PLH} ,	Propagation Delay	C _L = 50 pF					
t _{PHL}	Input to Output	V _{DIFF} = 2.5V	10	19	30	35	ns
		$V_{CM} = 0V$					

Symbol	Parameter	Conditions	Min	Тур	м	ax	Units
-,					DS26C32AT	DS26C32AM	1
t _{RISE} ,	Output Rise and	C _L = 50 pF					
t _{FALL}	Fall Times	V _{DIFF} = 2.5V		4	9	9	ns
		$V_{CM} = 0V$					
t _{PLZ} ,	Propagation Delay	C _L = 50 pF					
t _{PHZ}	ENABLE to Output	$R_L = 1000\Omega$		13	22	29	ns
		V _{DIFF} = 2.5V					
t _{PZL} ,	Propagation Delay	C _L = 50 pF					
t _{PZH}	ENABLE to Output	$R_{L} = 1000\Omega$		13	23	29	ns
		$V_{DIFF} = 2.5V$					

Note 1: Absolute Maximum Ratings are those values beyond which the safety of the device cannot be guaranteed. They are not meant to imply that the device should be operated at these limits. The table of "Electrical Characteristics" provides conditions for actual device operation.

Note 2: Unless otherwise specified, all voltages are referenced to ground.

Note 3: Unless otherwise specified, Min/Max limits apply over recommended operating conditions. All typicals are given for V_{CC} = 5V and T_A = 25°C.

Note 4: ESD Rating: HBM (1.5 kΩ, 100 pF)

Inputs ≥2000V

. All other pins ≥1000V

EIAJ (0Ω, 200 pF) ≥350V

Note 5: Ratings apply to ambient temperature at 25°C. Above this temperature derate N Package 13.16 mW/°C, J Package 15.38 mW/°C, M Package 9.52 mW/°C, E Package 12.04 mW/°C, and W package 6.94 mW/°C.

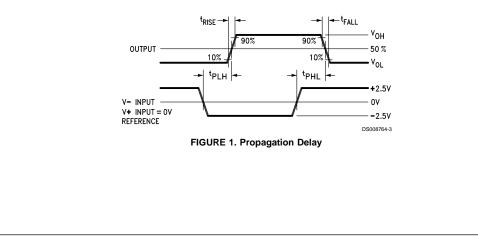
Comparison Table of Switching Characteristics into "LS-Type" Load

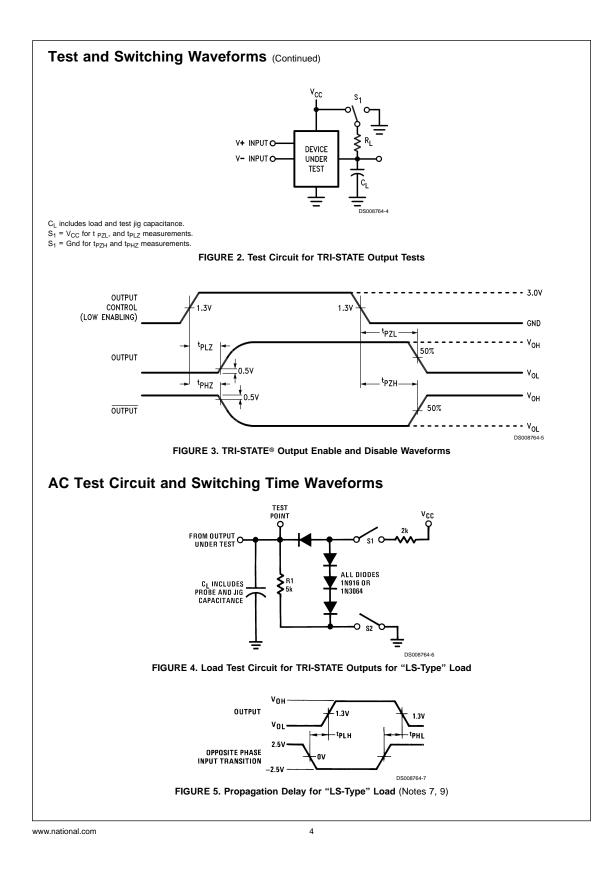
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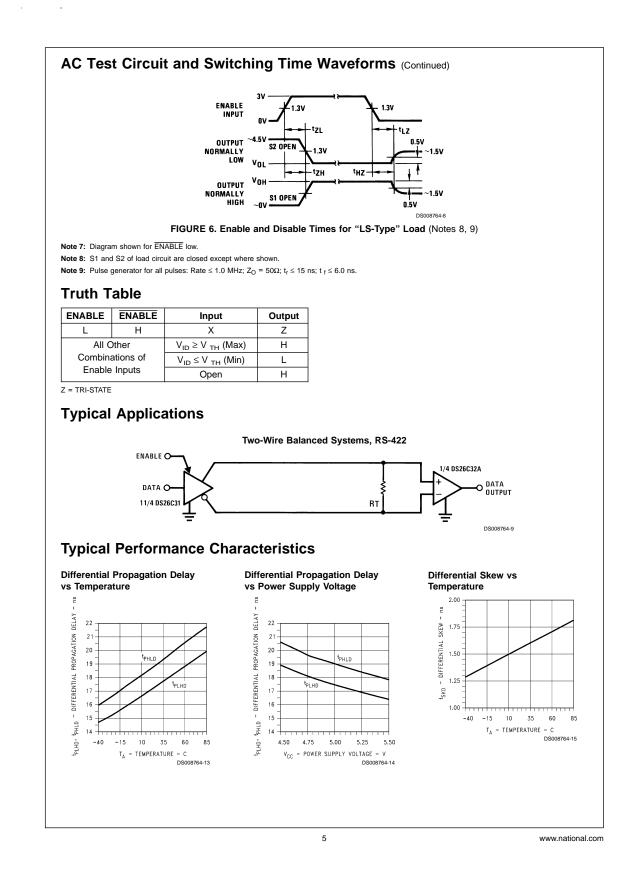
Symbol	Parameter	Conditions	DS26C32A	DS26LS32A	Units
			Тур	Тур	
t _{PLH}	Input to Output	C _L = 15 pF	17	23	ns
t _{PHL}			19	23	ns
t _{LZ}	ENABLE to Output	C _L = 5 pF	13	15	ns
t _{HZ}			12	20	ns
t _{ZL}	ENABLE to Output	C _L = 15 pF	13	14	ns
t _{zH}			13	15	ns

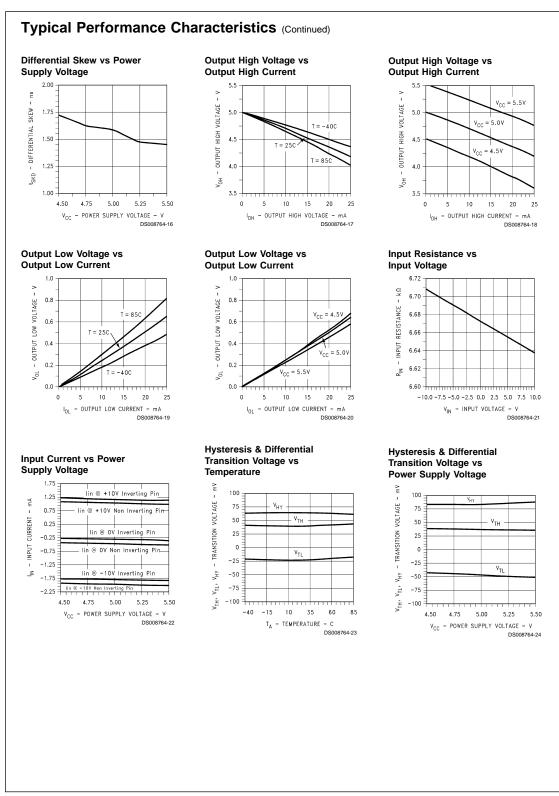
Note 6: This table is provided for comparison purposes only. The values in this table for the DS26C32A reflect the performance of the device, but are not tested or guaranteed.

Test and Switching Waveforms



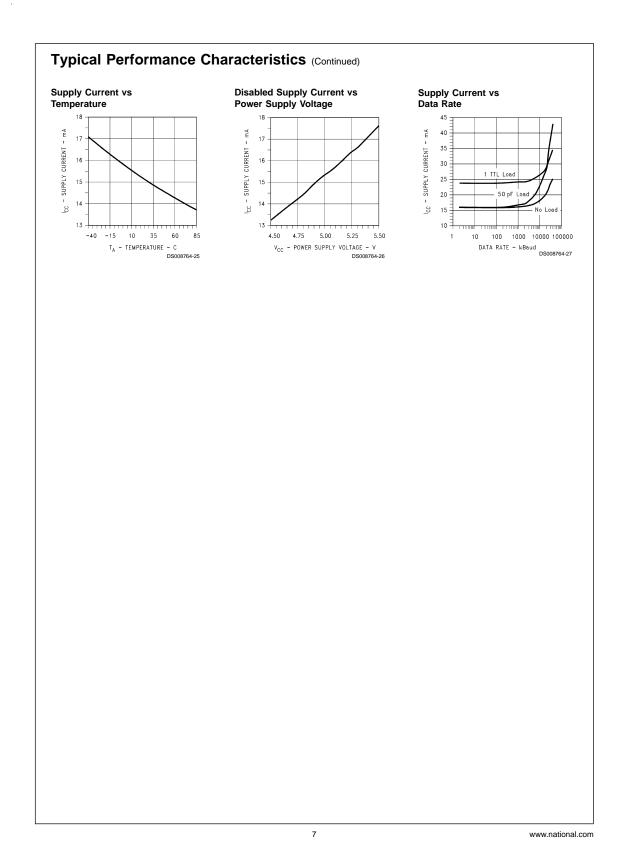


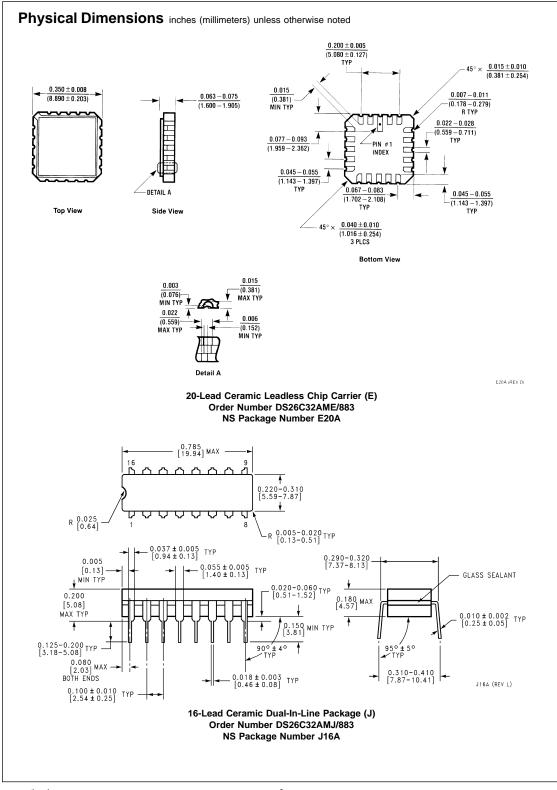


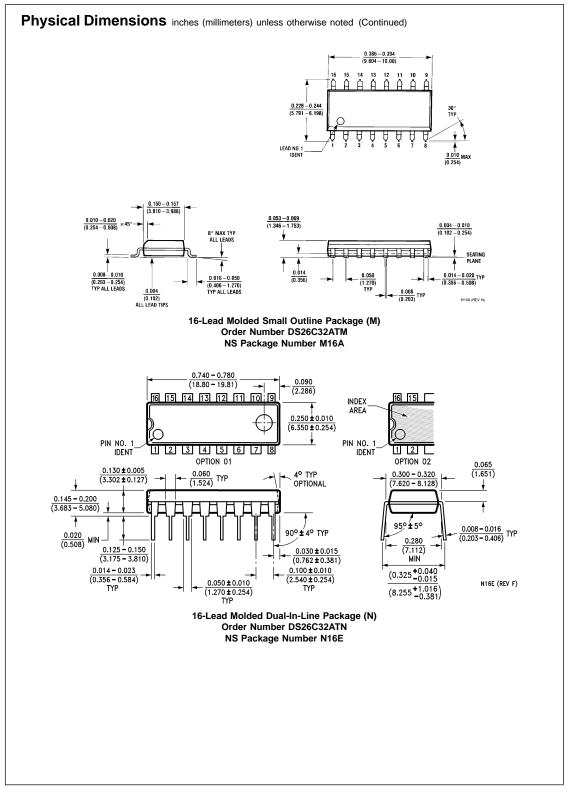


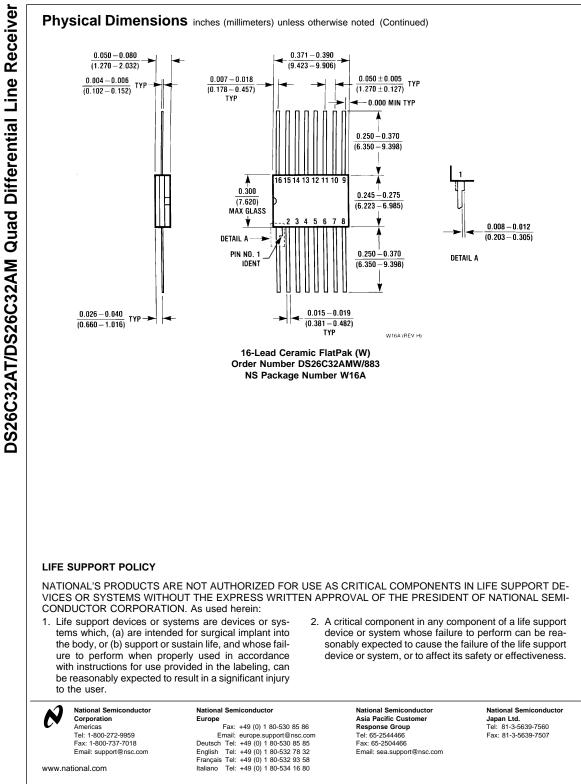
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6









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